DECLARATION OF COMPLIANCE
- ELV Declaration -

NXP Semiconductors Netherlands B.V. declares that its certified ELV compliant semiconductor products (including homogeneous sub-components – pins, casing, and internal parts) are designed to be:

- ELV compliant and meet the requirements of the EU-Directive 2000/53/EC of the European Parliament of 18 September 2000 (End of Live Vehicles, ELV) and its amendments.

ELV Restricted Substance	Allowable Limit
Cadmium and its compounds	100 ppm (0.01 weight %)
Mercury and its compounds	1000 ppm (0.1 weight %)
Hexavalent chromium and its compounds	1000 ppm (0.1 weight %)
Lead and its compounds	1000 ppm (0.1 weight %)

NXP ELV compliant semiconductor devices contain no more than 0.1% lead (Pb) by weight per homogeneous material, or else the devices may contain lead (Pb) for uses allowed by the ELV Directive, as amended. NXP might use any of the following ELV exemptions for ELV compliant semiconductor devices:

ELV Exemption	RoHS Exemption Reference	ELV Exemption Description
3	6(c)	Copper alloys containing up to 4 % lead by weight
8(e)	7(a)	Lead in high melting temperature type solders (i.e. lead-based alloys containing 85 % by weight or more lead)
8(a)	Non-RoHS compliant	Lead in solders to attach electrical and electronic components to electronic circuit boards and lead in finishes on terminations of components other than electrolyte aluminium capacitors, on component pins and on electronic circuit boards.*
10(a)	7(c)-I	Electrical and electronic components which contain lead in a glass or ceramic, in a glass or ceramic matrix compound, in a glass-ceramic material, or in a glass-ceramic matrix compound. This exemption does not cover the use of lead in: - glass in bulbs and glaze of spark plugs, - dielectric ceramic materials of components listed under 10(b), 10(c) and 10(d).
8(g)(i)	15	Lead in solders to complete a viable electrical connection between semiconductor die and carrier within integrated circuit flip chip packages**
8(g)(ii)	15(a)	Lead in solders to complete a viable electrical connection between the semiconductor die and the carrier within integrated circuit flip chip packages where that electrical connection consists of any of the following***: (i) a semiconductor technology node of 90 nm or larger; (ii) a single die of 300 mm2 or larger in any semiconductor technology node; (iii) stacked die packages with dies of 300 mm2 or larger, or silicon interposers of 300 mm2 or larger.

* Applies only to vehicles type approved prior to January 1st 2016, and spare parts for these vehicles. Applicability of the exemption is dependent on OEM application and final use.

** Valid for vehicles type approved before 1 October 2022 and spare parts for these vehicles. Applicability of the exemption is dependent on OEM application and final use.

*** Valid for vehicles type approved from 1 October 2022 and spare parts for these vehicles. Applicability of the exemption is dependent on OEM application and final use.

To facilitate customer requirements and to verify NXP semiconductor product compliance, NXP material content information is available here or by contacting the NXP ECO-Products team at eco-products@nxp.com.

For your convenience and immediate assistance, a spreadsheet may be downloaded from the material content link above. This document may be utilized for further processing in chemical management systems (e.g. IMDS).
In determining the ELV status of its products, NXP relies upon its suppliers' material content data certification for each homogenous material in the product(s) that they or their subcontractors provide. The signature below verifies that statements above, including but not limited to material composition data are valid and accurate to the best of our knowledge for NXP products in original sale condition. However, NXP cannot warrant that products from NXP's customers, in which such NXP products are incorporated, will in turn comply with this ELV Declaration.

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Edwin Bertotti
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